SiC Power Module

BSM400C12P3G202

Datasheet

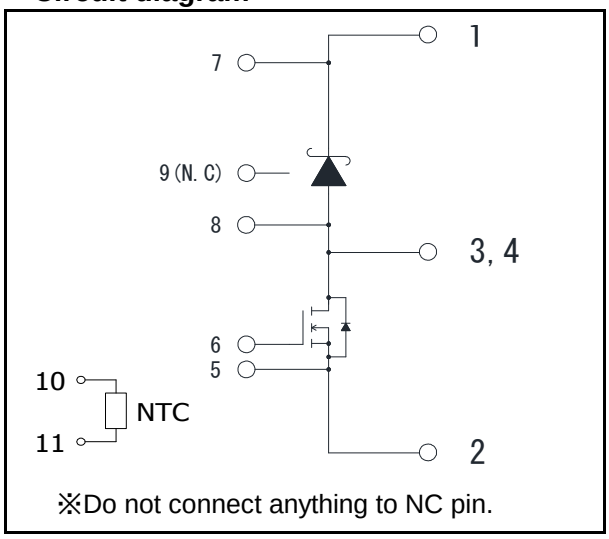
●Application

・Motor drive

・Converter

・Photovoltaics, wind power generation.

●Circuit diagram



※Do not connect anything to NC pin.

●Features

1) Low surge, low switching loss.

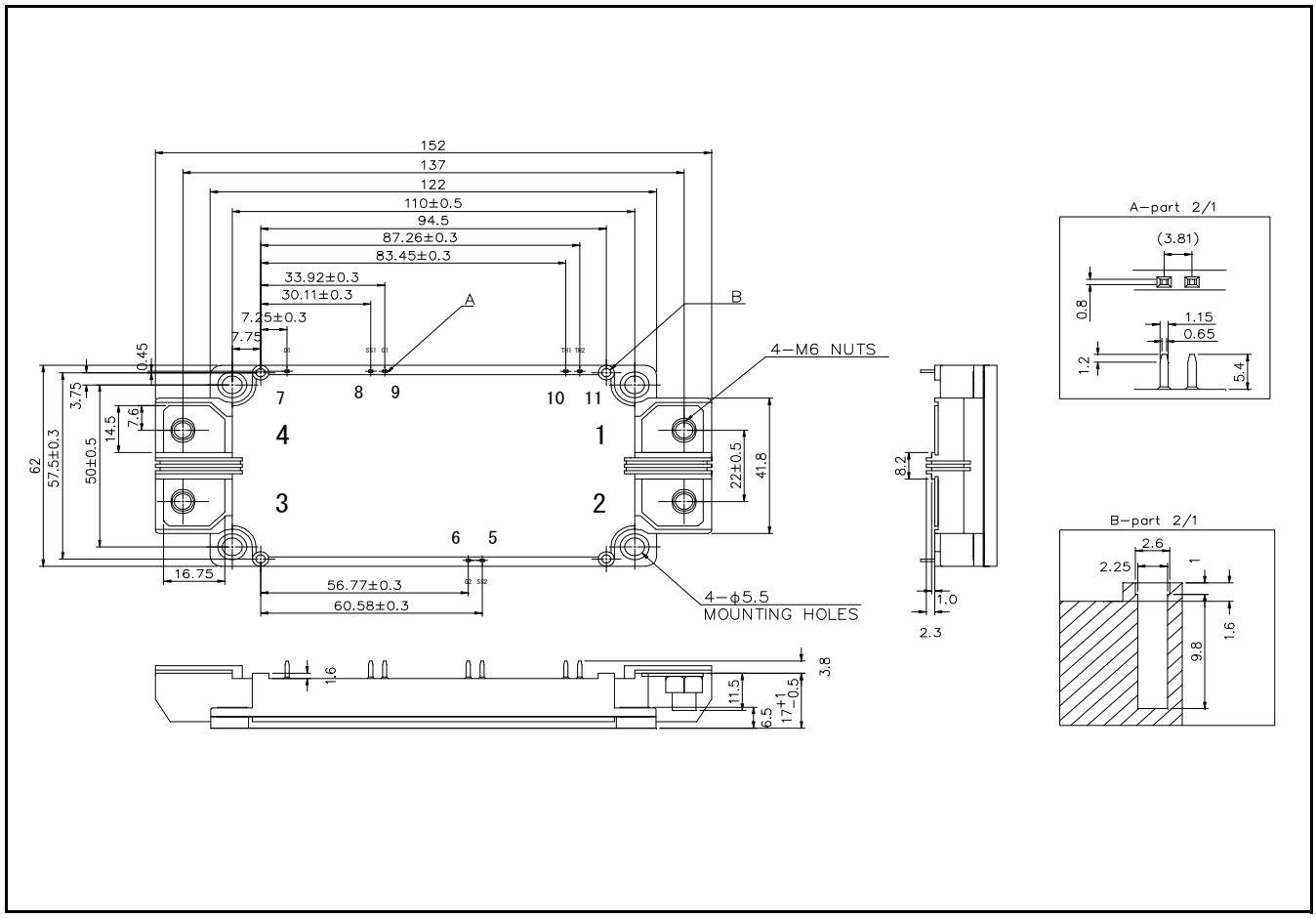
2) High-speed switching possible.

3) Reduced temperature dependence.

●Construction

This product is a chopper module consisting of SiC-UMOSFET and SiC-SBD from ROHM.

●Dimensions & Pin layout (Unit : mm)

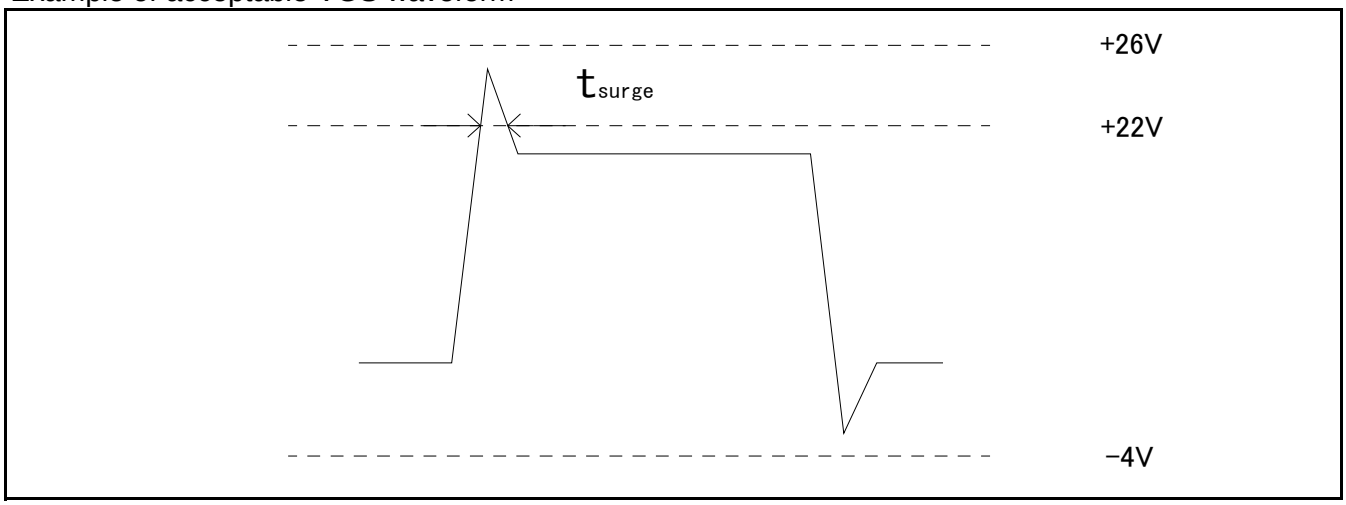


● **Absolute maximum ratings** (T_j = 25°C)

Parameter	Symbol	Conditions	Ratings	Unit
Drain - Source Voltage	V_{DSS}	G-S short	1200	V
Repetitive Reverse Voltage	V_{RRM}	Clamp diode	1200	
Gate - Source Voltage (+)	V_{GSS}	D-S short	22	
Gate - Source Voltage (-)	V_{GSS}	D-S short	-4	
G - S Voltage (t_{surge}<300nsec)	$V_{GSSsurge}$	D-S short	-4 to 26	
Drain Current Note 1)	I_D	DC(Tc=60°C) VGS=18V	358	A
	I_D	DC(Tc=32℃) VGS=18V	400	
	I_{DRM}	Pulse (Tc = 60°C） 1ms VGS=18V Note 2)	800	
Source Current Note 1)	I_S	DC(Tc=60°C) VGS=18V	358	
	I_S	DC(Tc=32°C) VGS=18V	400	
	I_{SRM}	Pulse (Tc = 60°C） 1ms VGS=18V Note 2)	800	
	I_{SRM}	Pulse (Tc = 60°C） 10us VGS=0V Note 2)	800	
Forward Current (clamp diode) Note 1)	I_F	DC(Tc = 60℃)	400	
	I_{FRM}	Pulse (Tc = 60℃） 1ms Note 2)	800	
Total Power Dissipation Note 3)	Ptot	Tc = 25°C	1570	W
Max Junction Temperature	Tjmax		175	°C
Junction Temperature	Tjop		-40 to 150	
Storage Temperature	Tstg		-40 to 125	
Isolation Voltage	Visol	Terminals to baseplate f = 60Hz AC 1 min.	2500	Vrms
Mounting Torque	-	Main Terminals : M6 screw	4.5	N・m
		Mounting to heat sink M5 screw	3.5	

Note 1) Case temperature (Tc) is defined on the surface of base plate just under the chips.
Note 2) Repetition rate should be kept within the range where temperature rise if die should not exceed Tjmax.
Note 3) Tj is less than 175°C.

Example of acceptable VGS waveform



●Electrical characteristics (T_j=25°C)

Parameter	Symbol	Conditions		Ratings Min.	Ratings Typ.	Ratings Max.	Unit
On-state static Drain-Source Voltage	V_{DS}(on)	ID=400A,VGS=18V	Tj=25°C	—	1.8	2.5	V
			Tj=125°C	—	2.6	—	
			Tj=150°C	—	3.0	4.5	
Drain Cutoff Current	I_{DSS}	V_{DS}=1200V,V_{GS}=0V		—	—	10	uA
Forward Voltage	V_F	I_F=400A	Tj=25°C	—	1.7	2.1	V
			Tj=125°C	—	2.0	—	
			Tj=150°C	—	2.1	3.4	
Reverse current	I_{RRM}	Clamp diode		—	—	4	mA
Gate-Source Threshold Voltage	V_{GS}(th)	V_{DS}=10V,I_D=106.8mA		2.7	—	5.6	V
Gate-Source Leak Current	I_{GSS}	V_{GS}=22V,V_{DS}=0V		—	—	0.5	μA
		V_{GS}=-4V,V_{DS}=0V		-0.5	—	—	
Switching Characteristics	td(on)	V_{GS}(on)=18V、V_{GS}(off)=0V V_{DS}=600V I_D=400A R_G(on)=1.0 ohm, R_G(off)=0.2 ohm Inductive load		—	55	—	ns
	tr			—	40	—	
	trr			—	25	—	
	td (off)			—	180	—	
	tf			—	45	—	
Input Capacitance	Ciss	V_{DS}=10V,V_{GS}=0V,200kHz		—	17	—	nF
Gate Registance	R_{Gint}	Tj=25°C		—	2.4	—	Ω
NTC Rated Resistance	R_{25}			—	5.0	—	kΩ
NTC B Value	$B_{50/25}$			—	3370	—	K
Stray Inductance	Ls			—	10.0	—	nH
Creepage Distance	-	Terminal to heat sink		—	16.7	—	mm
		Terminal to terminal		—	16.7	—	mm
Clearance Distance	-	Terminal to heat sink		—	12.0	—	mm
		Terminal to terminal		—	11.0	—	mm
Junction-to -Case Thermal Resistance	Rth(j-c)	UMOSFET(1/2 module) Note 4)		—	—	96	°C/kW
		SBD(1/2 module) Note 4)		—	—	80	
Case-to -heat sink Thermal Resistance	Rth(c-f)	Case to heat sink, per 1 module. Thermal grease applied. Note 5)		—	15	—	

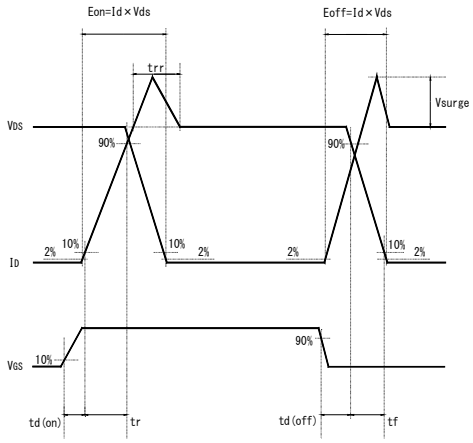
Note 4) Measurement of Tc is to be done at the point just under the chip.

Note 5) Typical value is measured by using thermally conductive grease of λ=0.9W/(m･K).

Note 6) SiC devices have lower short cuicuit withstand capability due to high current density. Please be advised to pay careful attention to short cuicuit accident and try to adjust protection time to shutdown them as short as possible.

Note 7) If the Product is used beyond absolute maximum ratings defined in the Specifications, as its internal structure may be dameged, please replace such Product with a new one.

＜Wavelength for Switching Test＞



●**Electrical characteristic curves** (Typical)

Fig.1 Output characteristic 25°C (TYP)

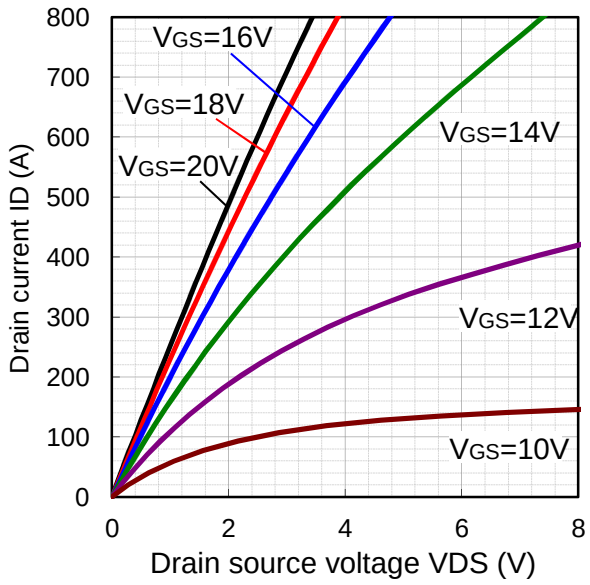


Fig.2 Drain source voltage characteristic (TYP)

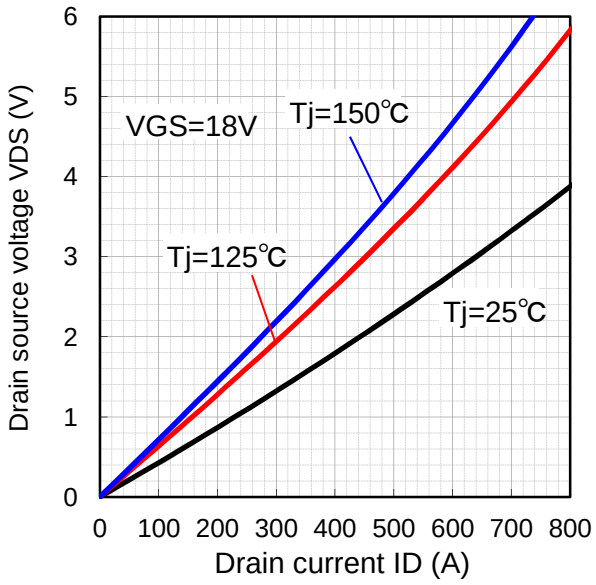


Fig.3 Drain source voltage characteristic 25°C (TYP)

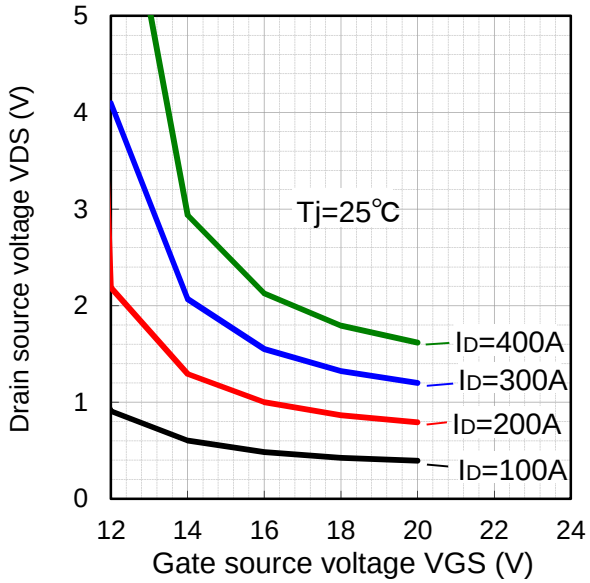
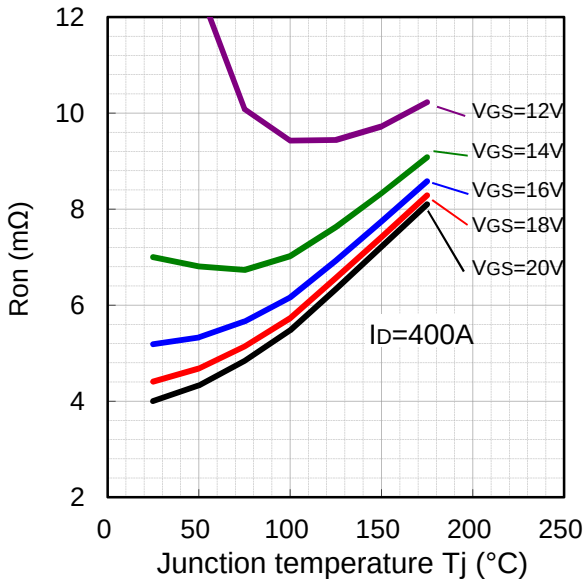


Fig.4 Ron vs Tj characteristic (TYP)



●**Electrical characteristic curves** (Typical)

Fig.5 Forward characteristic of Diode (TYP)

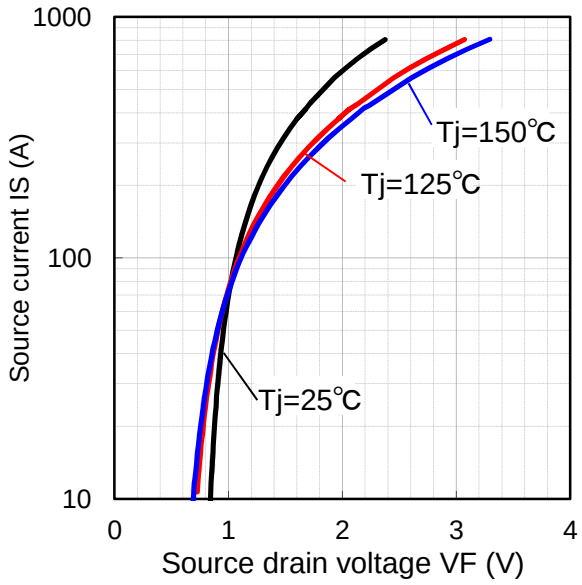


Fig.6 Forward characteristic of Diode (TYP)

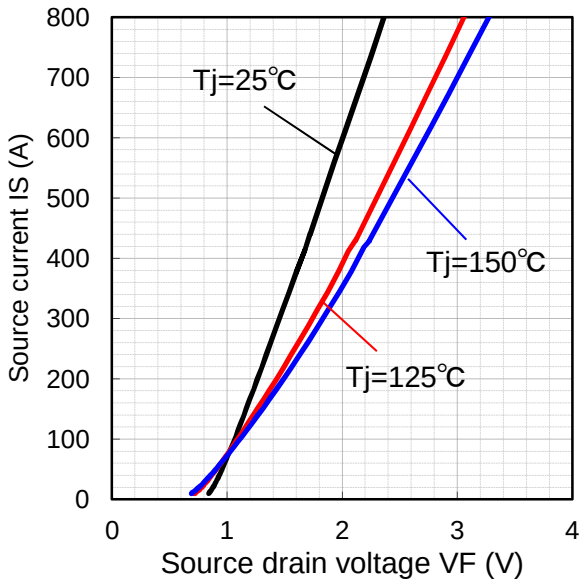


Fig.7 Drain Current vs Gate Voltage (TYP)

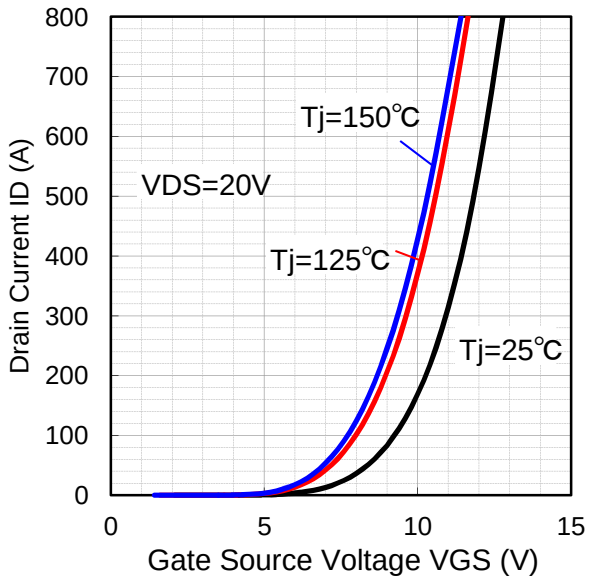
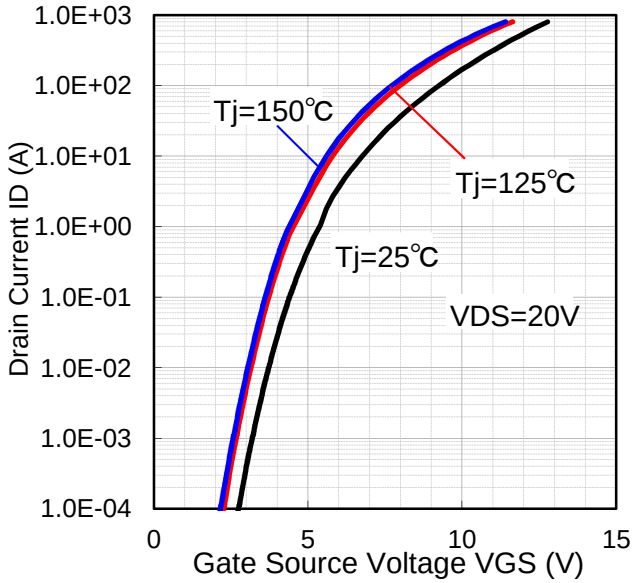


Fig.8 Drain Current vs Gate Voltage (TYP)



●Electrical characteristic curves (Typical)

Fig.9 Switching time vs drain current at 25°C (TYP)

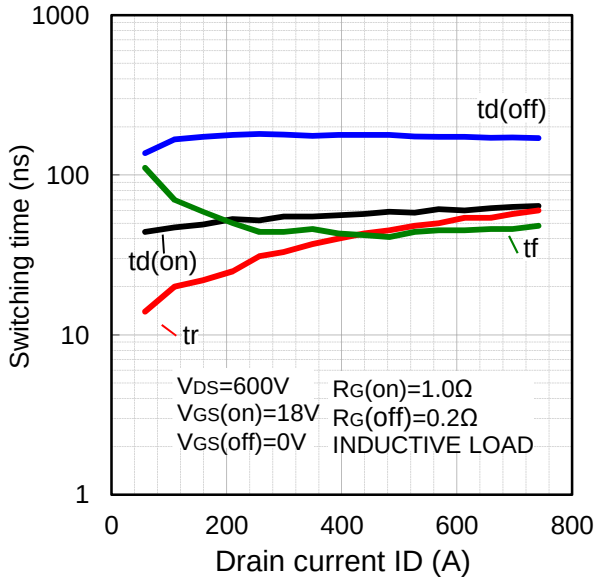


Fig.10 Switching time vs drain current at 125°C (TYP)

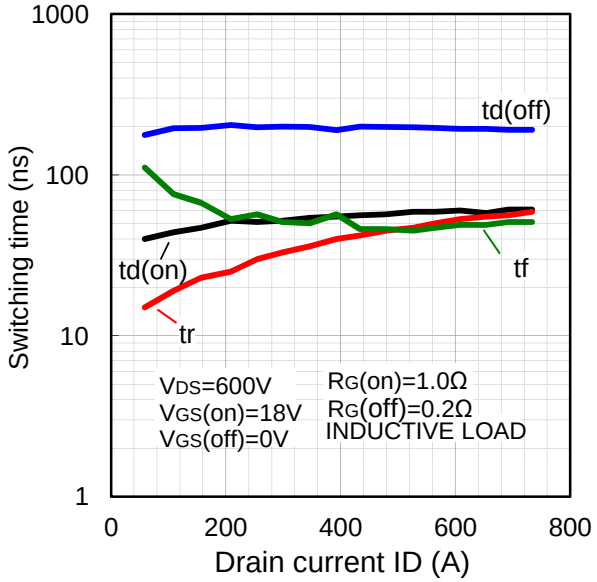


Fig.11 Switching time vs drain current at 150°C (TYP)

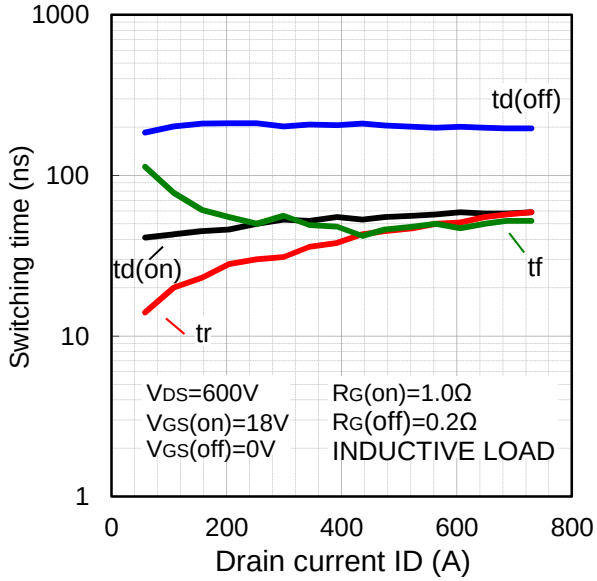
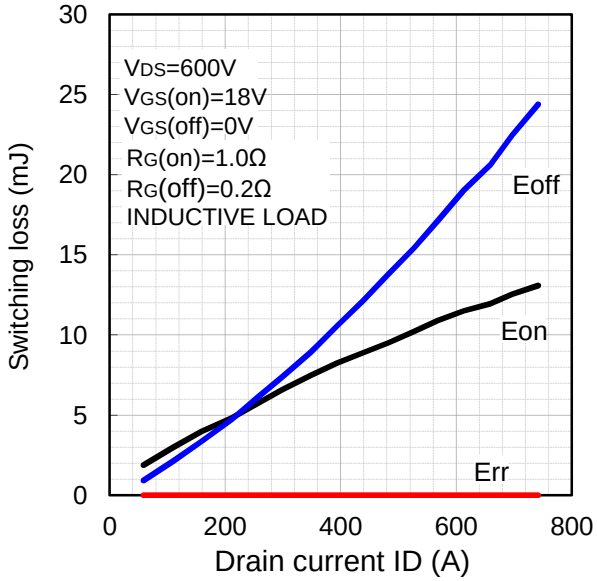


Fig.12 Switching loss vs drain current at 25°C (TYP)



●Electrical characteristic curves (Typical)

Fig.13 Switching loss vs drain current at 125°C (TYP)

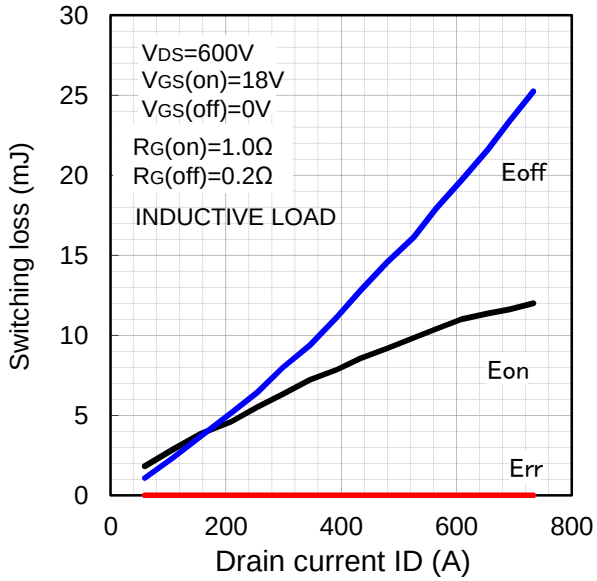


Fig.14 Switching loss vs drain current at 150°C (TYP)

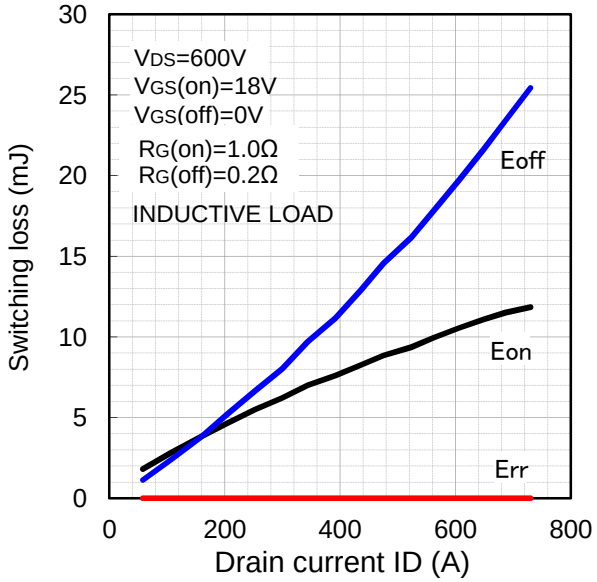


Fig.15 Recovery characteristic vs drain current at 25°C (TYP)

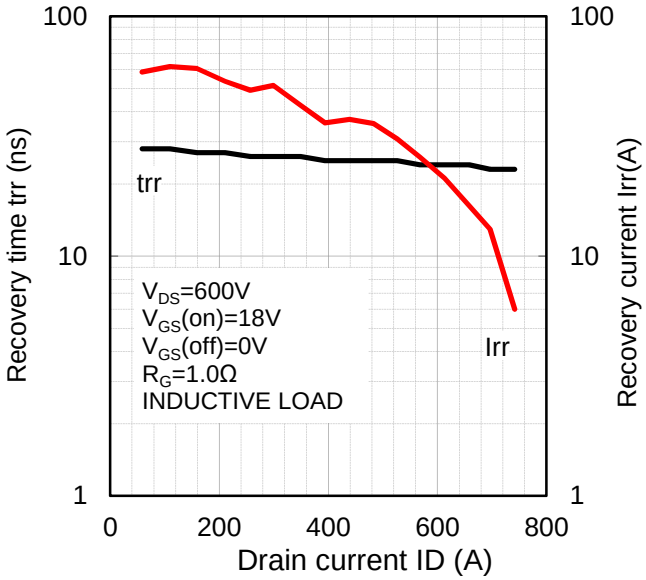
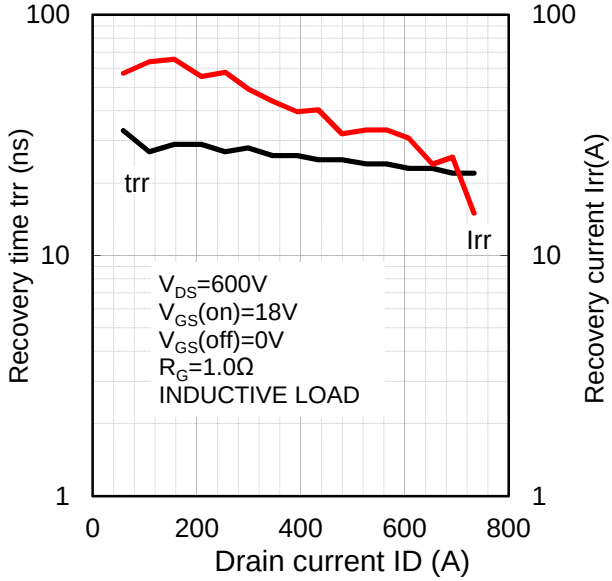


Fig.16 Recovery characteristic vs drain current at 125°C (TYP)



●Electrical characteristic curves (Typical)

Fig.17 Recovery characteristic vs drain current at 150°C (TYP)

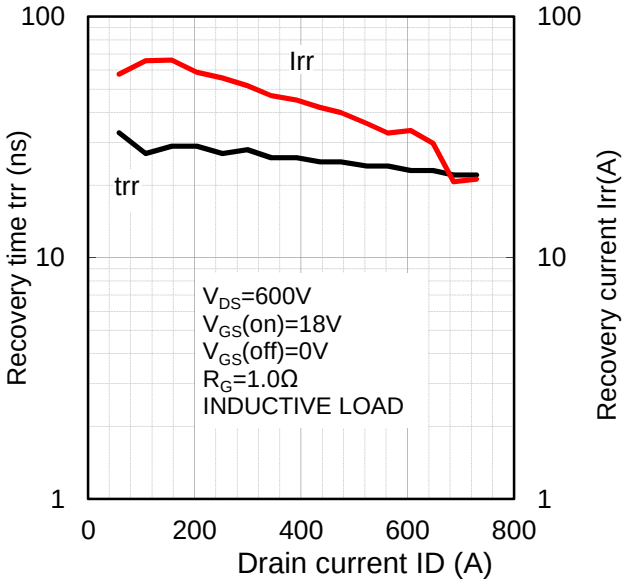


Fig.18 Switching time vs gate resistance at 25°C (TYP)

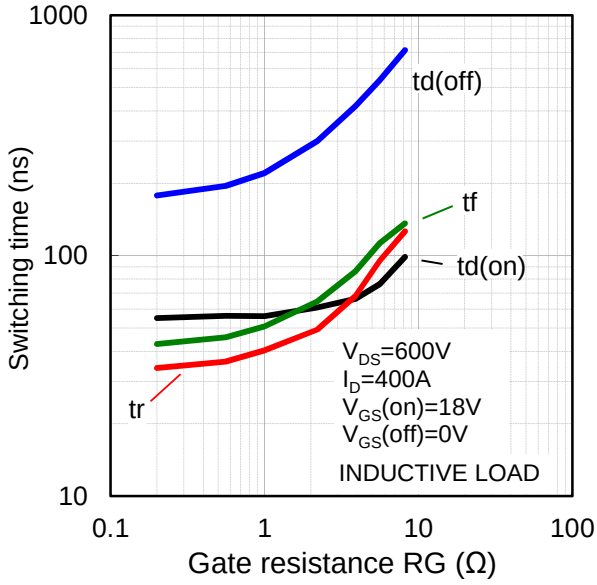


Fig.19 Switching time vs gate resistance at 125°C (TYP)

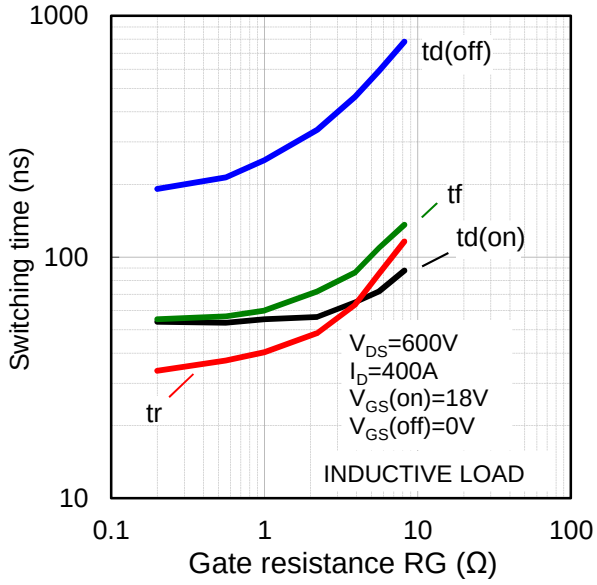
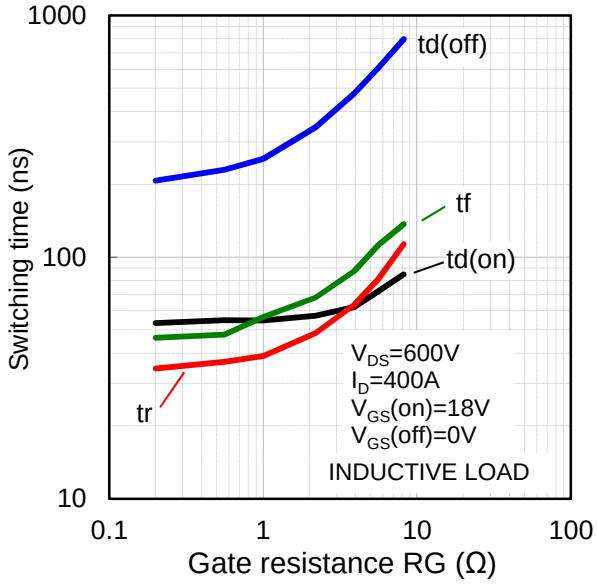


Fig.20 Switching time vs gate resistance at 150°C (TYP)



●**Electrical characteristic curves** (Typical)

Fig.21 Switching loss vs gate resistance at 25°C (TYP)

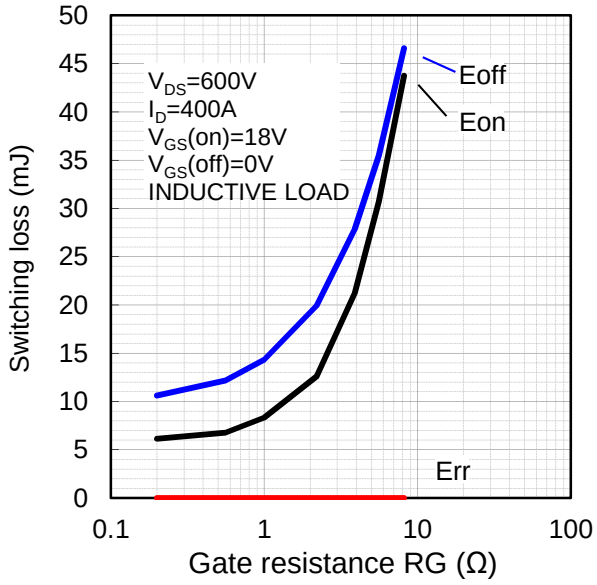


Fig.22 Switching loss vs gate resistance at 125°C (TYP)

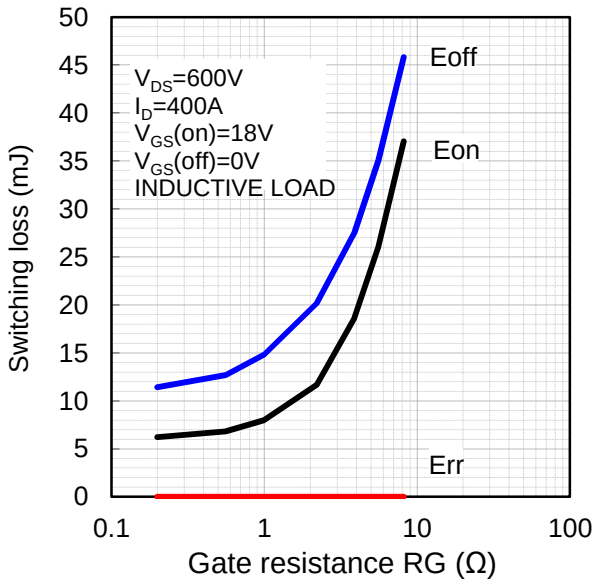
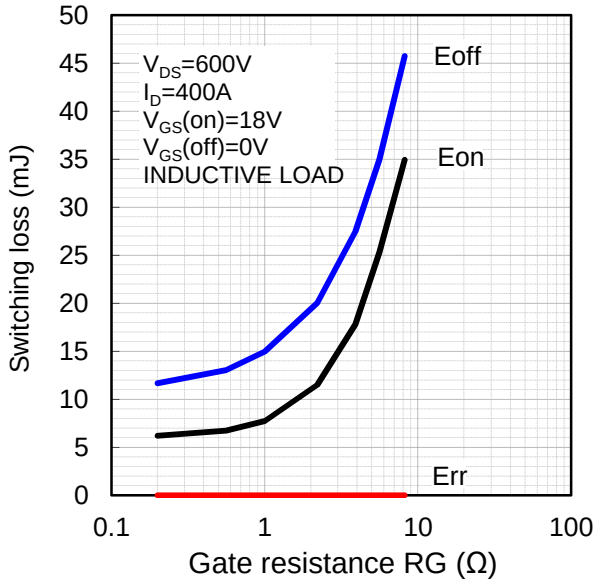


Fig.23 Switching loss vs gate resistance at 150°C (TYP)



●**Electrical characteristic curves** (Typical)

Fig.24 Capacitance vs Drain source voltage (TYP)

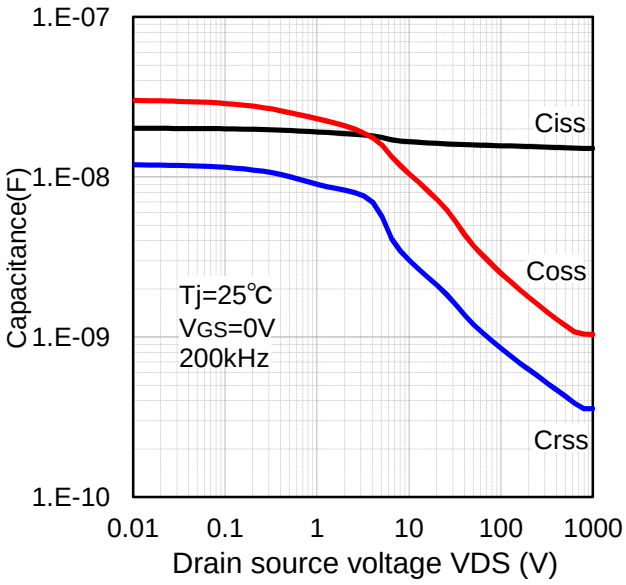


Fig.25 Gate charge characteristic (TYP)

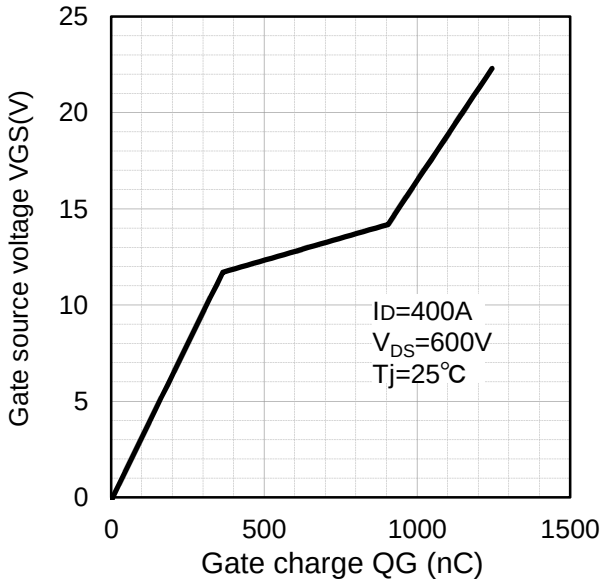
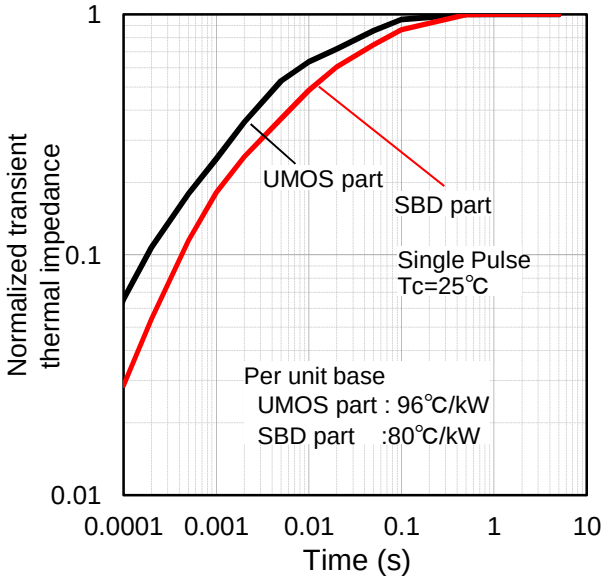


Fig.26 Transient thermal impedance (TYP)



Notes

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2) Before you use our Products, please contact our sales representative and verify the latest specifications.

3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors.
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7) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative : transportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, and power transmission systems.

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BSM400C12P3G202 - Web Page

Part Number	BSM400C12P3G202
Package	G
Unit Quantity	4
Minimum Package Quantity	4
Packing Type	Corrugated Cardboard
Constitution Materials List	inquiry
RoHS	Yes